

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

# 2SB1375

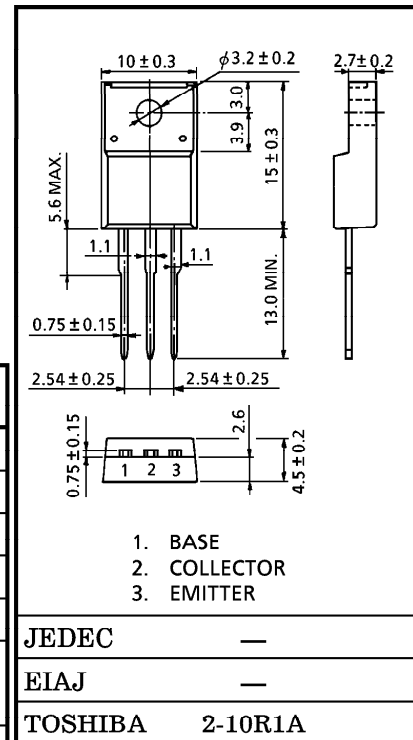
AUDIO FREQUENCY POWER AMPLIFIER

Unit in mm

- Low Saturation Voltage :  $V_{CE(sat)} = -1.5V$  (Max.)  
( $I_C = -2A, I_B = -0.2A$ )
- High Power Dissipation :  $P_C = 25W$  ( $T_c = 25^\circ C$ )
- Collector Metal (Fin) is Covered with Mold Resin
- Complementary to 2SD2012

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CB0}$	-60	V
Collector-Emitter Voltage		$V_{CEO}$	-60	V
Emitter-Base Voltage		$V_{EB0}$	-7	V
Collector Current		$I_C$	-3	A
Base Current		$I_B$	-0.5	A
Collector Power Dissipation	$T_a = 25^\circ C$	$P_C$	2.0	W
	$T_c = 25^\circ C$		25	
Junction Temperature		$T_j$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	-55~150	$^\circ C$



JEDEC	—
EIAJ	—
TOSHIBA	2-10R1A

Weight : 1.7g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -60V, I_E = 0$	—	—	-10	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -7V, I_C = 0$	—	—	-10	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-60	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -5V, I_C = -0.5A$	100	—	320	
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -2A$	15	—	—	
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$	—	-1.0	-1.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -5V, I_C = -0.5A$	—	-0.75	-1.0	V
Transition Frequency	$f_T$	$V_{CE} = -5V, I_C = -0.5A$	—	9	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	50	—	pF

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